

General Description



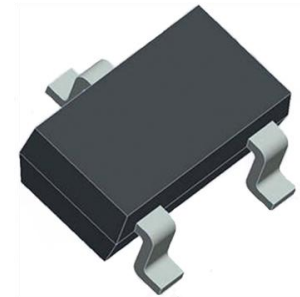
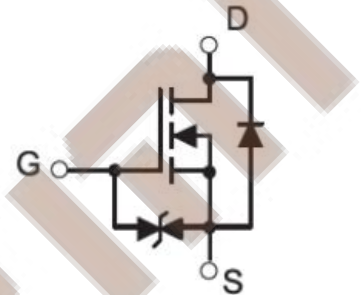
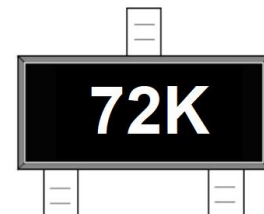
V_R	$R_{DS(ON) MAX}$	$I_D Max.$
60V	3.0Ω@10V	340mA
	3.2Ω@4.5V	

Features

- High density cell design for low RDS(ON)
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- Load Switch for Portable Devices
- DC/DC Converter
- ESD protected

Mechanical Data

- SOT-523 Small Outline Plastic Package.
- Epoxy UL: 94V-0.
- Mounting Position: Any.



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
2N7002KT	SOT-523	72K	3000

Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbols	Rating	Units
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	VGS	±20	V
Continuous Drain Current	ID	0.34	A
Pulsed Drain Current (note 1)	IDM	0.80	A
Power Dissipation	PD	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-50-+150	°C
Thermal Resistance From Junction to Ambient	R θ JA	625	°C/W

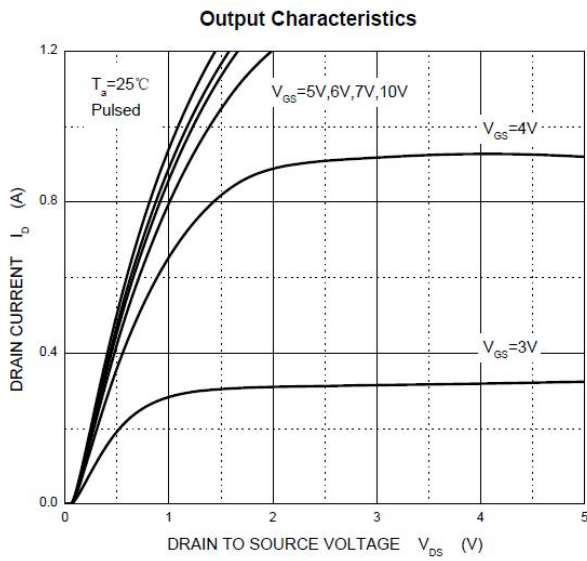
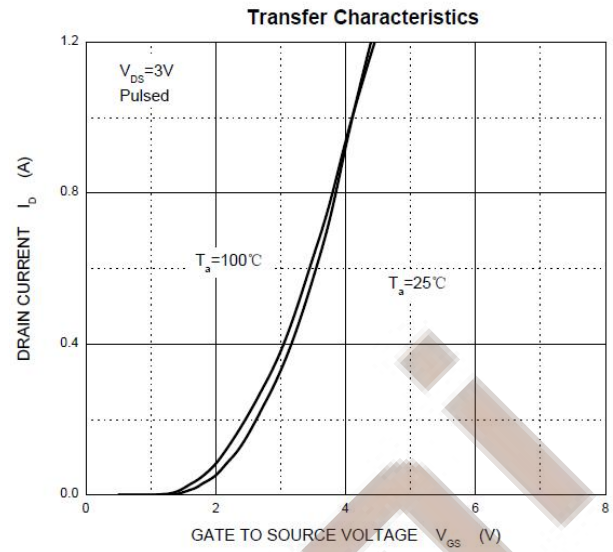
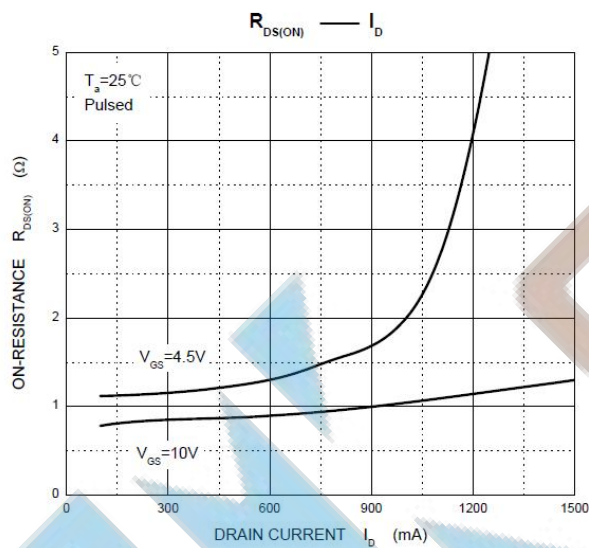
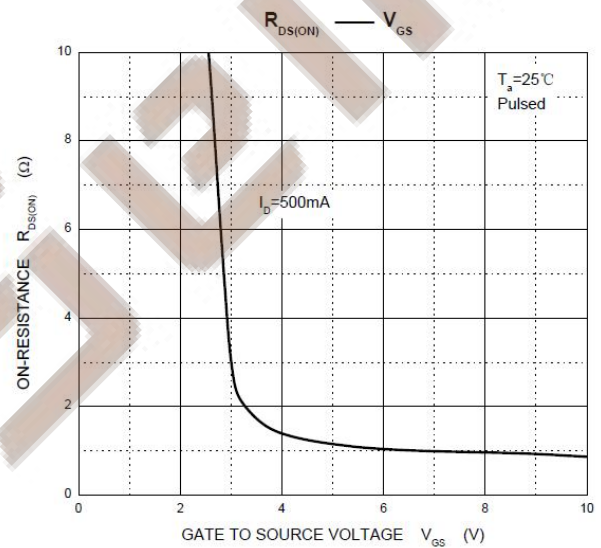
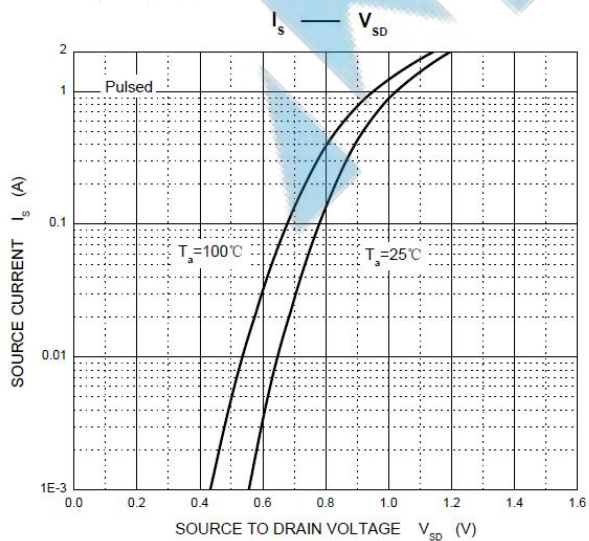
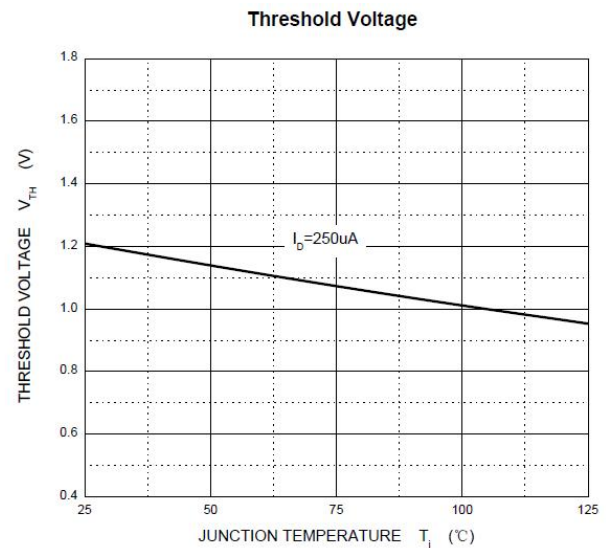
Electrical Characteristics (Tj=25°C,unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	V(BR)DSS	VGS=0V, ID=250uA	60			V
Gate-Threshold voltage(note 2)	V GS (th)	VDS= VGS, ID=1mA	1.0	1.3	2.5	V
Gate-body Leakage	IGSS	VDS=0V, VGS= ± 20V			± 10	uA
Zero Gate Voltage Drain current	IDSS	VDS=48V, VGS=0V			1	uA
On-state Drain Current	ID(ON)	VGS=10V, VDS=7V	500			mA
Drain-Source On-Resistance (note2)	RDS(ON)	VGS=10V, ID=500mA		2.2	3.0	Ω
		VGS=4.5V, IC=200mA		2.4	3.2	
DYNAMIC PARAMETERS (note 3)						
Input capacitance	Ciss	VDS=10V, VGS=0V,f=1MHz			40	pF
Output capacitance	Coss				30	
Reverse Transfer capacitance	Crss				10	
SWITCHING PARAMETERS (note 3)						
Turn-on Delay Time	td(on)	VGS=10V,VDD=50V, RG=50 Ω			10	ns
Turn-off Delay Time	td(off)	RL=250 Ω , RGS=50 Ω			15	ns
Reverse Recovery Time	trr	VGS=0V,VR=25V, IS=300mA		30		ns
Recovered Charge	BVGSO	IS= ± 1mA	± 21.5		± 32	V
DRAIN-SOURCE DIODE						
Diode Forward Voltage(note 2)	VSD	Is=300mA, VGS=0V			1.5	V
Continuous Diode Forward Current	IS				0.2	A
Pulsed Diode Forward(note 1)	ISM				0.53	A

Notes:

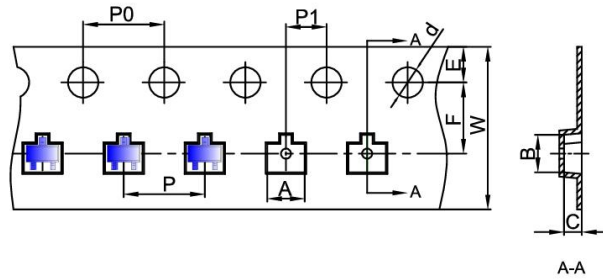
- 1.Repetitive rating : Pulse width limited by junction temperature
- 2.Pulse width ≤300us, duty cycle ≤2%.
- 3.Guaranteed design, not subject to production testing.

Typical Characteristics



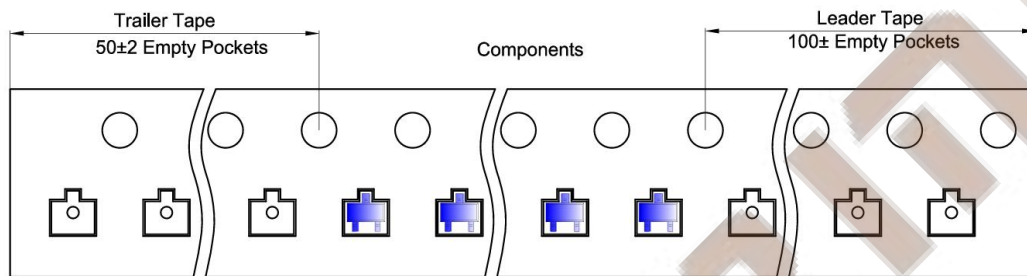
Package Information

Carrier Dimension(mm)

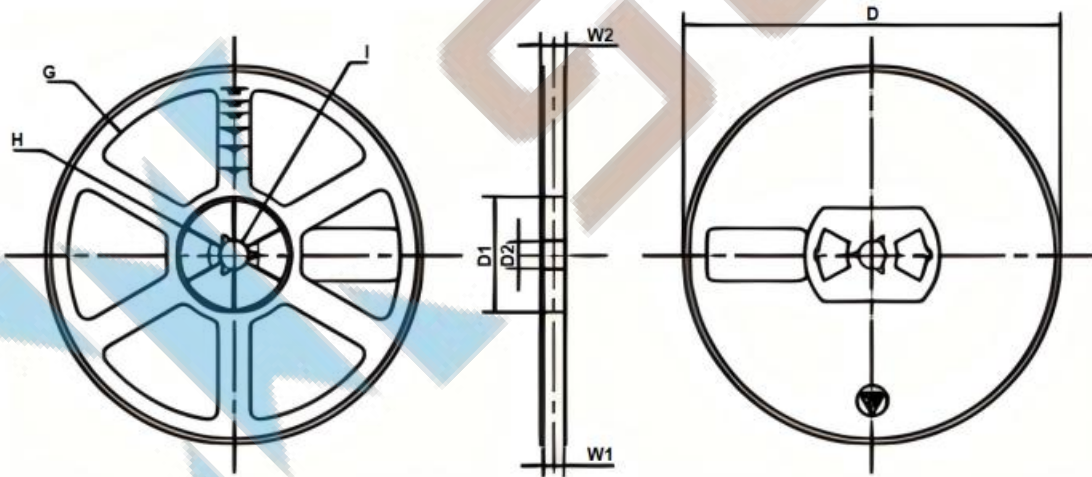


Dimensions are in millimeter

Pkg Type	A	B	C	d	E	F	P0	P	P1	W
SOT-523	1.85	1.85	0.875	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00



Reel Dimension(mm)



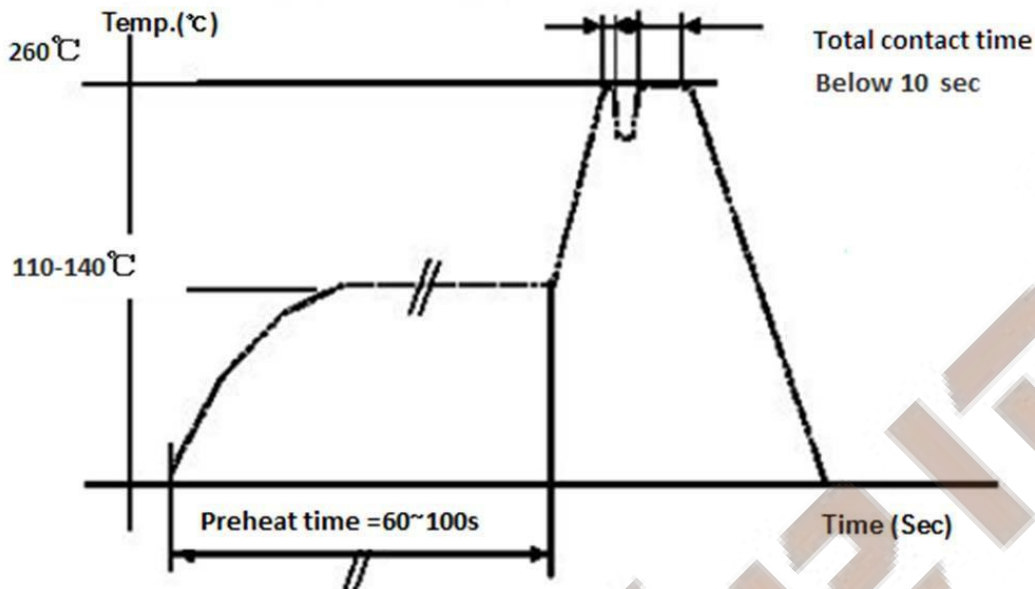
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Φ178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30
Tolerance	±2	±1	±1	±1	±1	±1	±1	±1

Package Specifications

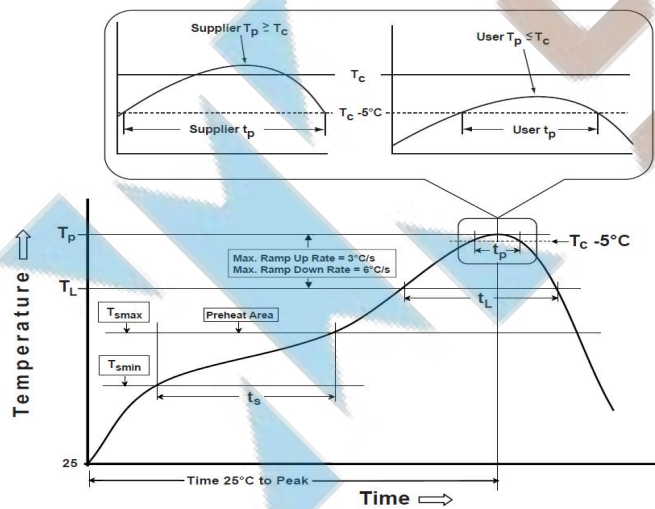
Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (Kpcs)	Box Size (mm)	QTY/Box (Kpcs)	Carton Size (mm)	Q'TY/Carton (Kpcs)
SOT523	7'	178	3	210*208*203	45	440*400*230	180

Recommended Soldering Profile for Rectifier Diodes (Pb Free)

a) Wave Soldering Profile



b) Reflow Soldering Profile (Pb Free Application), refer to IPC/JEDEC J-STD-020

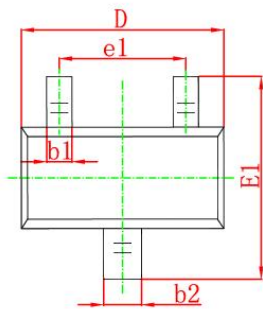
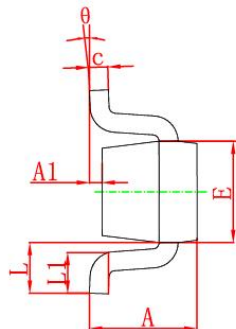
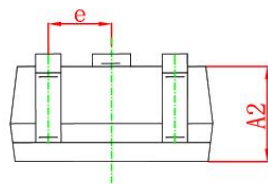


Preheat/Soak Temperature Min (Tsmin) Temperature Max (Tsmax) Time (ts) from (Tsmin to Tsmax)	50 °C 200 °C 60-120 seconds
Melting Point of Solder (Sn Ag Cu)	217°C
Ramp-up Rate to 217°C(Melting Point of Solder)	3°C/sec
Time at Temp.>217°C (Melting Point of Solder)	60~150 Sec
Peak Temperature	255±5°C
Time within 5°Cbelow Peak Temp.	20~40 Sec
Cooling Rate	6°C/sec (max)
Time from 25°C to Peak Temp.	8min (max)

c) Manual Soldering

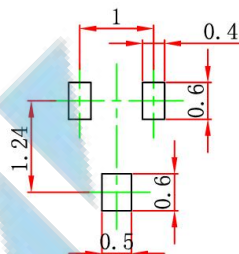
When using an electric soldering iron for manual soldering, it is recommended that the temperature does not exceed 300°C and the soldering time is less than 10 seconds.

Package Mechanical Data



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

Disclaimer

The information presented in this document is for reference only. Yancheng **Xirun Semiconductor Co., Ltd** reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), **Xirun Semiconductor** or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.x-semi.cn](http://www.x-semi.cn) , or consult your nearest **Xirun Semiconductor's** sales office for further assistance.